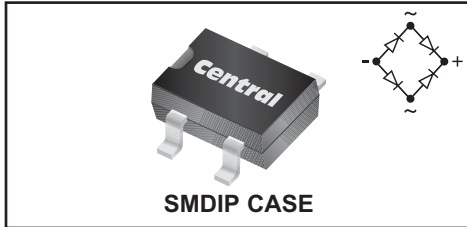


**CBR1-D020S SERIES****SURFACE MOUNT  
1 AMP  
SILICON BRIDGE RECTIFIER**[www.centrasemi.com](http://www.centrasemi.com)**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CBR1-D020S series types are silicon full wave bridge rectifiers mounted in a durable epoxy surface mount molded case, utilizing glass passivated chips.

NOTE: Also available in Fast Recovery, please contact factory for details.

**MARKING: FULL PART NUMBER****MAXIMUM RATINGS:**(T<sub>A</sub>=25°C unless otherwise noted)

	SYMBOL	CBR1-D020S	CBR1-D040S	CBR1-D060S	CBR1-D080S	CBR1-D100S	UNITS
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	200	400	600	800	1000	V
DC Blocking Voltage	V <sub>R</sub>	200	400	600	800	1000	V
RMS Reve	V <sub>R(RMS)</sub>	140	280	420	560	700	V
Average Forward Current (T <sub>A</sub> =50°C)	I <sub>O</sub>			1.0			A
Peak Forward Surge Current	I <sub>FSM</sub>			50			A
Rating for Fusing (t<8.35ms)	I <sup>2</sup> t			10			A <sup>2</sup> s
Operating and Storage Junction Temperature	T <sub>J</sub> , T <sub>stg</sub>			-65 to +150			°C

**ELECTRICAL CHARACTERISTICS PER DIODE: (T<sub>A</sub>=25°C unless otherwise noted)**

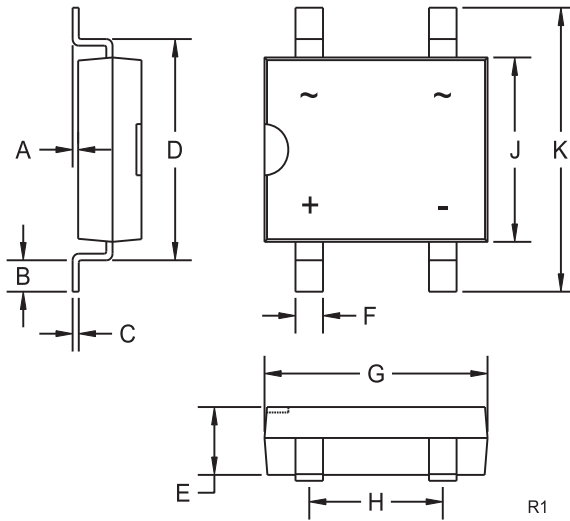
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I <sub>R</sub>	V <sub>R</sub> =Rated V <sub>RRM</sub>			10	μA
I <sub>R</sub>	V <sub>R</sub> =Rated V <sub>RRM</sub> , T <sub>A</sub> =125°C			0.5	mA
V <sub>F</sub>	I <sub>F</sub> =1.0A			1.1	V
C <sub>J</sub>	V <sub>R</sub> =4.0V, f=1.0MHz		25		pF

R3 (4-January 2010)

**CBR1-D020S SERIES**  
**SURFACE MOUNT**  
**1 AMP**  
**SILICON BRIDGE RECTIFIER**



**SMDIP CASE - MECHANICAL OUTLINE**



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.008	0.10	0.20
B	0.040	0.060	1.02	1.52
C	0.009		0.23	
D	0.290	0.310	7.37	7.87
E	0.086	0.098	2.18	2.49
F	0.038	0.042	0.97	1.07
G	0.316	0.335	8.03	8.51
H	0.195	0.205	4.95	5.21
J	0.245	0.255	6.22	6.48
K	0.360	0.410	9.14	10.41

SMDIP (REV: R1)

**MARKING: FULL PART NUMBER**

R3 (4-January 2010)